

MCSO2EHW

2.5V High Frequency Oscillator for Extreme Environments

- Suitable for Avionics, Down-hole, Geothermal etc
- Extreme temperature ranges up to 210°C
- High stability & low ageing under extremes
- High shock & vibration resistance
- Optional tinned pads (Ag/Cu/Zn)



CONFIGURABLE OPTIONS	
Parameter	Option Code
Frequency	
Frequency stability	
* see note below	
Any	
±100ppm max over -55 to +125°C	С
±150ppm max over -55 to +150°C	E
±300ppm max over -55 to +175°C	D
±400ppm max over -55 to +210°C	G
Enable / disable function	
Any	
None (pad 1 NC)	
Active (control via pad 1)	E
Terminations	
Any	
Gold plated pads	
Tinned Ag/Cu/Zn	Т

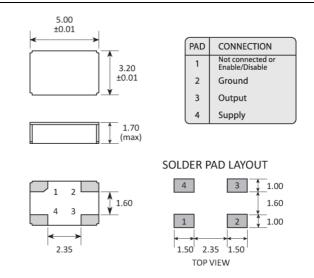
^{*} Frequency stability is inclusive of calibration @ 25°C, operating temperature range, supply voltage change, load change and long term ageing (1,000hrs at T_{MAX}).



SPECIFICATIONS

Dimensions 5.0 x 3.2 x 1.7mm Supply voltage (V _{DD}) +2.5V (±5%) Storage temperature range -65 to +125°C Supply current 15mA max Driving ability CMOS Load 3pF min, 47pF max Logic levels '0' level = +0.4V max '1' level = V _{DD} -0.5V min Start up time 5ms max Waveform symmetry 40:60 max @ 50%V _{DD} Rise / fall time 3ns max (15pF, 10~90%V _{P-P}) Shock resistance 10,000g, 0.3ms, ½ sine Vibration resistance 80g rms 10.0 ~ 2,000Hz	Frequency range	20.0 ~ 100MHz
Storage temperature range -65 to +125°C Supply current 15mA max Driving ability CMOS Load 3pF min, 47pF max Logic levels '0' level = +0.4V max '1' level = V _{DD} -0.5V min Start up time 5ms max Waveform symmetry 40:60 max @ 50%V _{DD} Rise / fall time 3ns max (15pF, 10~90%V _{P-P}) Shock resistance 10,000g, 0.3ms, ½ sine Vibration resistance 80g rms 10.0 ~ 2,000Hz	Dimensions	5.0 x 3.2 x 1.7mm
Supply current 15mA max Driving ability CMOS Load 3pF min, 47pF max Logic levels '0' level = +0.4V max '1' level = V _{DD} -0.5V min Start up time 5ms max Waveform symmetry 40:60 max @ 50%V _{DD} Rise / fall time 3ns max (15pF, 10~90%V _{P-P}) Shock resistance 10,000g, 0.3ms, ½ sine Vibration resistance 80g rms 10.0 ~ 2,000Hz	Supply voltage (V _{DD})	+2.5V (±5%)
Driving ability CMOS Load 3pF min, 47pF max Logic levels '0' level = +0.4V max '1' level = V _{DD} -0.5V min Start up time 5ms max Waveform symmetry 40:60 max @ 50%V _{DD} Rise / fall time 3ns max (15pF, 10~90%V _{P-P}) Shock resistance 10,000g, 0.3ms, ½ sine Vibration resistance 80g rms 10.0 ~ 2,000Hz	Storage temperature range	-65 to +125°C
Load 3pF min, 47pF max Logic levels '0' level = +0.4V max '1' level = V _{DD} -0.5V min Start up time 5ms max Waveform symmetry 40:60 max @ 50%V _{DD} Rise / fall time 3ns max (15pF, 10~90%V _{P-P}) Shock resistance 10,000g, 0.3ms, ½ sine Vibration resistance 80g rms 10.0 ~ 2,000Hz	Supply current	15mA max
Logic levels '0' level = $+0.4V$ max '1' level = V_{DD} -0.5V min Start up time 5ms max Waveform symmetry 40:60 max @ $50\%V_{DD}$ Rise / fall time 3ns max ($15pF$, $10\sim90\%V_{P-P}$) Shock resistance 10,000g, $0.3ms$, ½ sine Vibration resistance 80g rms $10.0\sim2,000$ Hz	Driving ability	CMOS
$'1' \ level = V_{DD} - 0.5V \ min$ $Start \ up \ time$ $5ms \ max$ $Waveform \ symmetry$ $40:60 \ max \ (0.50\% V_{DD})$ $Rise \ / \ fall \ time$ $3ns \ max \ (15pF, \ 10\sim90\% V_{P-P})$ $Shock \ resistance$ $10,000g, \ 0.3ms, \ \frac{1}{2} \ sine$ $Vibration \ resistance$ $80g \ rms \ 10.0 \sim 2,000 \ Hz$	Load	3pF min, 47pF max
Start up time 5ms max Waveform symmetry 40:60 max @ 50%V _{DD} Rise / fall time 3ns max (15pF, 10~90%V _{P-P}) Shock resistance 10,000g, 0.3ms, ½ sine Vibration resistance 80g rms 10.0 ~ 2,000Hz	Logic levels	'0' level = +0.4V max
Waveform symmetry $40:60 \text{ max} \ \textcircled{0} 50\% \text{V}_{DD}$ Rise / fall time $3 \text{ns} \text{ max} \ (15 \text{pF}, 10 \sim 90\% \text{V}_{P-P})$ Shock resistance $10,000 \text{g}, 0.3 \text{ms}, \frac{1}{2} \text{ sine}$ Vibration resistance $80 \text{g rms} \ 10.0 \sim 2,000 \text{Hz}$		'1' level = V_{DD} -0.5V min
Rise / fall time 3ns max (15pF, $10\sim90\%V_{P-P}$) Shock resistance 10,000g, 0.3ms, ½ sine Vibration resistance 80g rms $10.0\sim2,000$ Hz	Start up time	5ms max
Shock resistance 10,000g, 0.3ms, ½ sine Vibration resistance 80g rms 10.0 ~ 2,000Hz	Waveform symmetry	40:60 max @ 50%V _{DD}
Vibration resistance 80g rms 10.0 ~ 2,000Hz	Rise / fall time	3ns max (15pF, 10~90%V _{P-P})
50 ₀ 5 10.0 2/0001.12	Shock resistance	10,000g, 0.3ms, ½ sine
2000 10	Vibration resistance	80g rms 10.0 ~ 2,000Hz
Soldering condition 260°C, 10 sec max	Soldering condition	260°C, 10 sec max

PACKAGE DRAWING



A 47nF ceramic capacitor must be connected between GND and VDD

Dimensions in mm

ORDERING INFORMATION

To request a quotation for the MCSO2EHW please use the configurable options form to choose the options you require and then submit your configured product to our team. Our expert advisers are always happy to help with your requirements and can be contacted on +44 1460 256 100 or at sales@golledge.com.

Following product selection you will be issued with a seven character Golledge part number. Your Golledge part number is the internationally accepted Golledge manufacturing part number (MPN) that should be used for all project documentation, including bills of materials (BoMs) and purchase orders.

If you have any queries regarding any of our documentation our dedicated sales team will be happy to help.

ENABLE / DISABLE FUNCTION

Input (pad 1)	Output (pad 3)
Open	Enabled
'1' level	Enabled
'0' level	No clock

Reaction time <1µs

HANDLING & STORAGE



Human Body Model (HBM) 1A (250V to <500V)

CONSTRUCTION

Ceramic base and lid



Moisture Sensitivity Level (MSL): 1 (or not applicable)



COMPLIANCE



Lead-free (< 0.1% by weight)



RoHS compliant with no exemptions. See our

declaration



REACH compliant. See our statement



Au Ta Sn W Free of conflict minerals. See our declaration



Free of Halogens. <u>See our declaration</u>



Free of Ozone-depleting substances. <u>See our</u>

declaration